



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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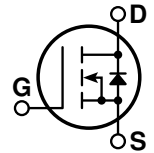
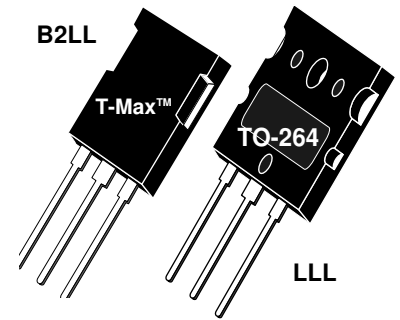
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



POWER MOS 7[®] MOSFET

Power MOS 7[®] is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7[®] by significantly lowering $R_{DS(ON)}$ and Q_g . Power MOS 7[®] combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge, Q_g
- Increased Power Dissipation
- Easier To Drive
- Popular T-MAX™ or TO-264 Package




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Parameter | APT50M65B2LL_LLL | UNIT |
|----------------|--|------------------|---------------------|
| V_{DSS} | Drain-Source Voltage | 500 | Volts |
| I_D | Continuous Drain Current @ $T_C = 25^\circ\text{C}$ | 67 | Amps |
| I_{DM} | Pulsed Drain Current ^① | 268 | |
| V_{GS} | Gate-Source Voltage Continuous | ± 30 | Volts |
| V_{GSM} | Gate-Source Voltage Transient | ± 40 | |
| P_D | Total Power Dissipation @ $T_C = 25^\circ\text{C}$ | 694 | Watts |
| | Linear Derating Factor | 5.5 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_L | Lead Temperature: 0.063" from Case for 10 Sec. | 300 | |
| I_{AR} | Avalanche Current ^① (Repetitive and Non-Repetitive) | 67 | Amps |
| E_{AR} | Repetitive Avalanche Energy ^① | 50 | mJ |
| E_{AS} | Single Pulse Avalanche Energy ^④ | 3000 | |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|---|-----|-----|-----------|---------------|
| BV_{DSS} | Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu\text{A}$) | 500 | | | Volts |
| $R_{DS(on)}$ | Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 33.5A$) | | | 0.065 | Ohms |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{DS} = 500V, V_{GS} = 0V$) | | | 100 | μA |
| | Zero Gate Voltage Drain Current ($V_{DS} = 400V, V_{GS} = 0V, T_C = 125^\circ\text{C}$) | | | 500 | |
| I_{GSS} | Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$) | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5mA$) | 3 | | 5 | Volts |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT50M65 B2LL - LLL

| Symbol | Characteristic | Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|------------------------------|--|-----|------|-----|---------|
| C_{iss} | Input Capacitance | $V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$ | | 7010 | | pF |
| C_{oss} | Output Capacitance | | | 1390 | | |
| C_{rss} | Reverse Transfer Capacitance | | | 87 | | |
| Q_g | Total Gate Charge ③ | $V_{GS} = 10V$ $V_{DD} = 250V$ $I_D = 67A @ 25^\circ C$ | | 141 | | nC |
| Q_{gs} | Gate-Source Charge | | | 40 | | |
| Q_{gd} | Gate-Drain ("Miller") Charge | | | 70 | | |
| $t_{d(on)}$ | Turn-on Delay Time | RESISTIVE SWITCHING $V_{GS} = 15V$ $V_{DD} = 250V$ $I_D = 67A @ 25^\circ C$ $R_G = 0.6\Omega$ | | 12 | | ns |
| t_r | Rise Time | | | 28 | | |
| $t_{d(off)}$ | Turn-off Delay Time | | | 29 | | |
| t_f | Fall Time | | | 30 | | |
| E_{on} | Turn-on Switching Energy ⑥ | INDUCTIVE SWITCHING @ 25°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 67A, R_G = 3\Omega$ | | 1035 | | μJ |
| E_{off} | Turn-off Switching Energy | | | 845 | | |
| E_{on} | Turn-on Switching Energy ⑥ | INDUCTIVE SWITCHING @ 125°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 67A, R_G = 3\Omega$ | | 1556 | | |
| E_{off} | Turn-off Switching Energy | | | 1013 | | |

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|----------|--|-----|------|-----|---------|
| I_S | Continuous Source Current (Body Diode) | | | 67 | Amps |
| I_{SM} | Pulsed Source Current ① (Body Diode) | | | 268 | |
| V_{SD} | Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -67A$) | | | 1.3 | Volts |
| t_{rr} | Reverse Recovery Time ($I_S = -67A, di_S/dt = 100A/\mu s$) | | 680 | | ns |
| Q_{rr} | Reverse Recovery Charge ($I_S = -67A, di_S/dt = 100A/\mu s$) | | 17.0 | | μC |
| dv/dt | Peak Diode Recovery dv/dt ⑤ | | | 8 | V/ns |

THERMAL CHARACTERISTICS

| Symbol | Characteristic | MIN | TYP | MAX | UNIT |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case | | | 0.18 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient | | | 40 | |

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting $T_j = +25^\circ C$, $L = 1.34mH$, $R_G = 25\Omega$, Peak $I_L = 67A$

⑤ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -67A$ $di/dt \leq 700A/\mu s$ $V_R \leq 500V$ $T_J \leq 150^\circ C$

⑥ E_{on} includes diode reverse recovery. See figures 18, 20.

APT Reserves the right to change, without notice, the specifications and information contained herein.

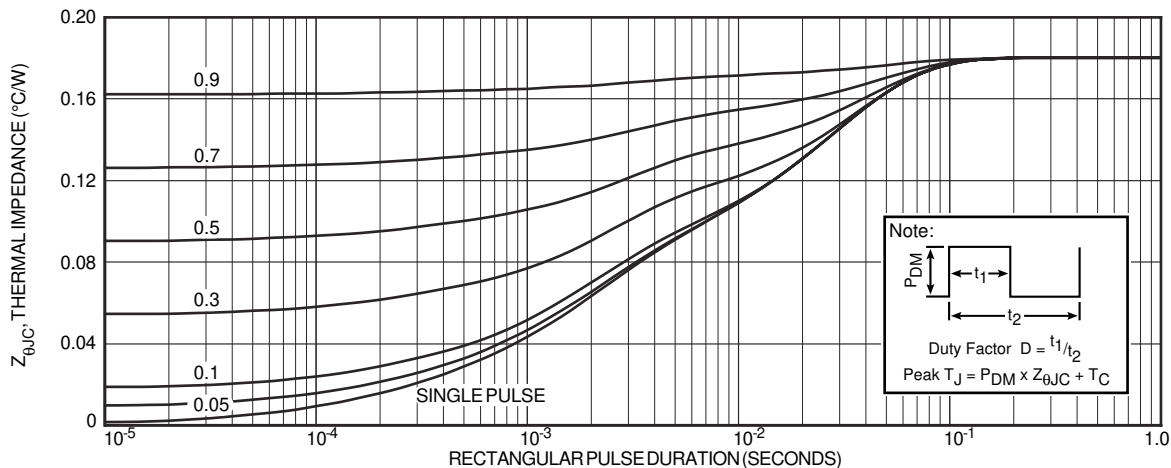


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Typical Performance Curves

APT50M65B2LL - LLL

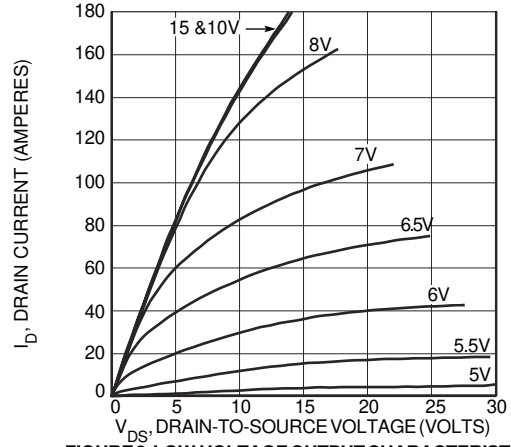
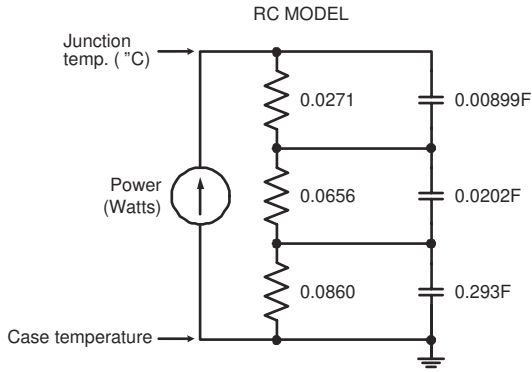


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

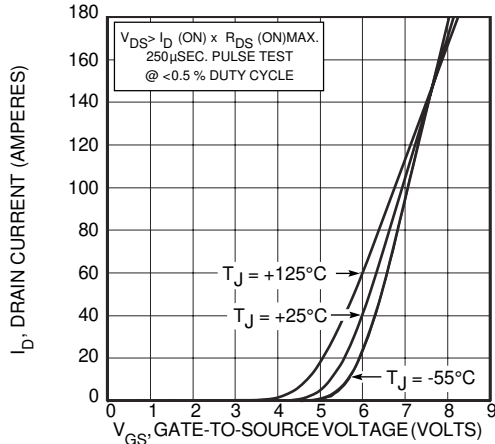


FIGURE 4, TRANSFER CHARACTERISTICS

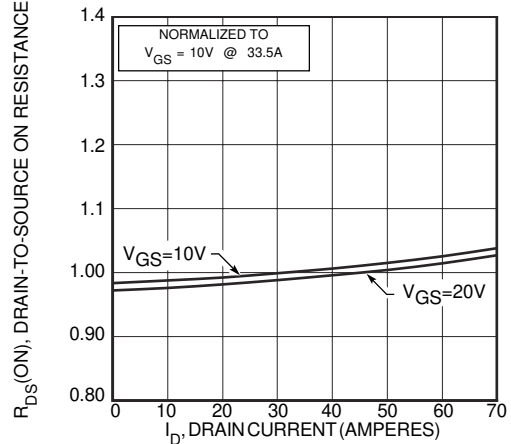


FIGURE 5, $R_{DS(\text{ON})}$ vs DRAIN CURRENT

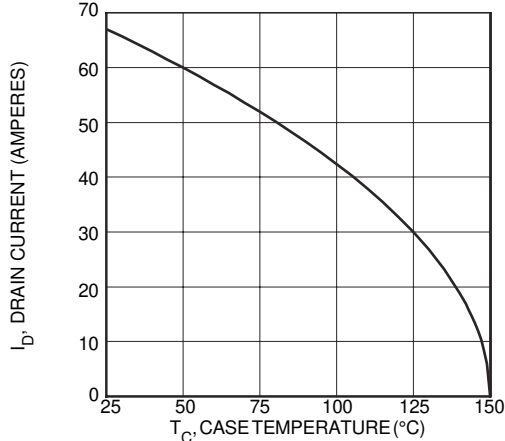


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

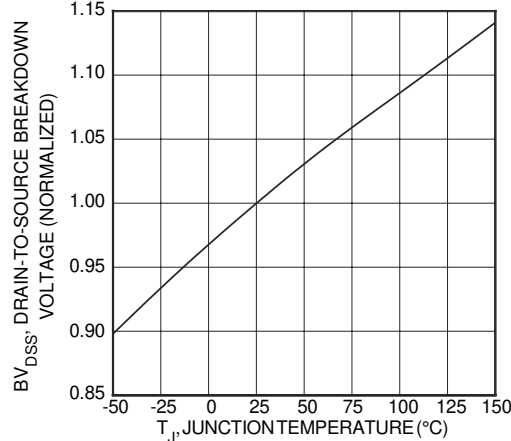


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

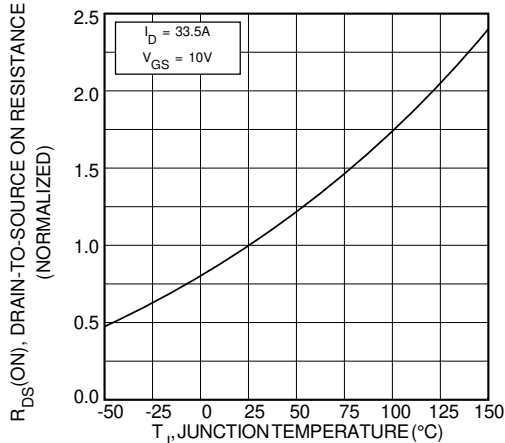


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

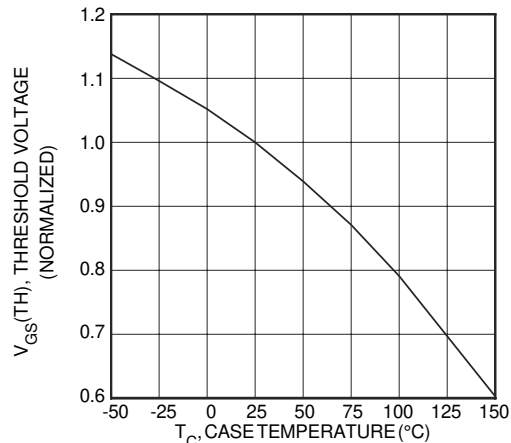


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

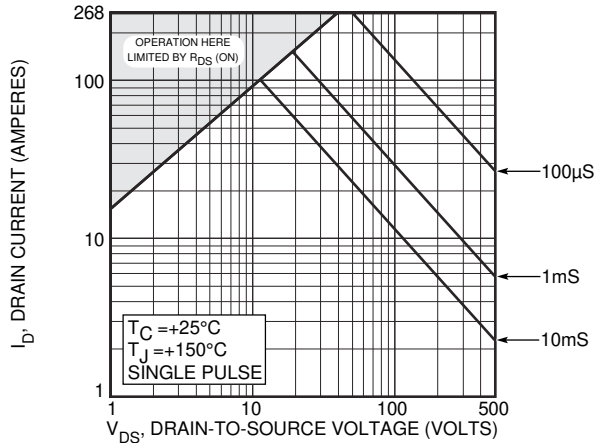


FIGURE 10, MAXIMUM SAFE OPERATING AREA

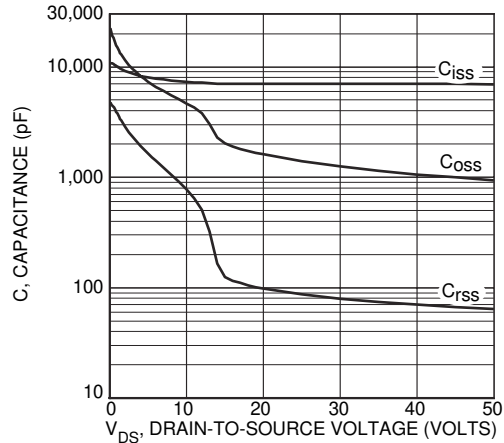


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

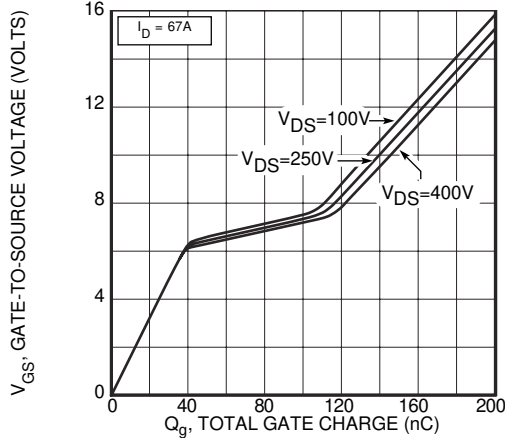


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

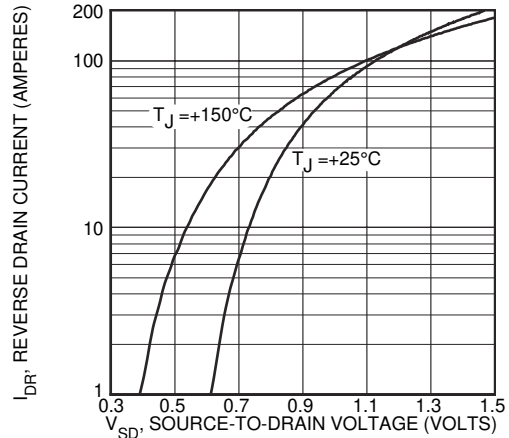


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

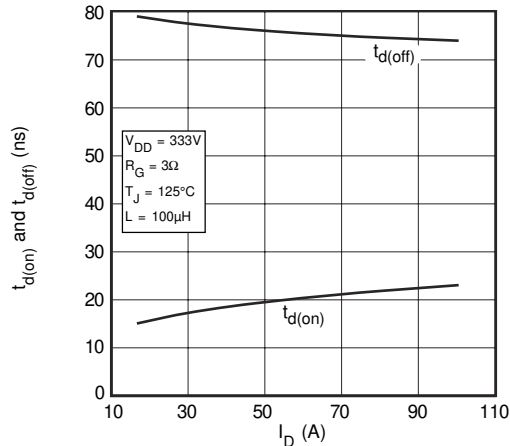


FIGURE 14, DELAY TIMES vs CURRENT

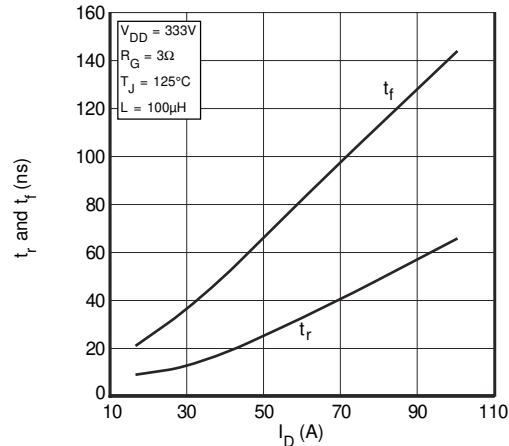


FIGURE 15, RISE AND FALL TIMES vs CURRENT

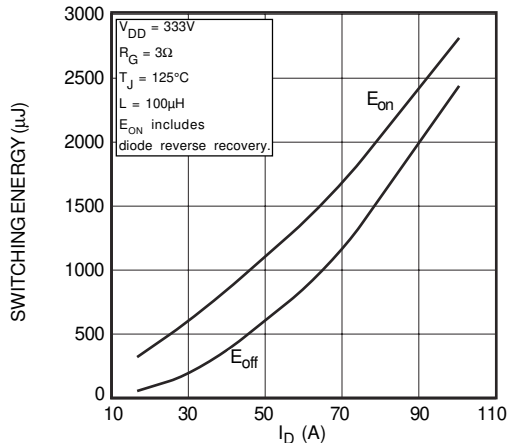


FIGURE 16, SWITCHING ENERGY vs CURRENT

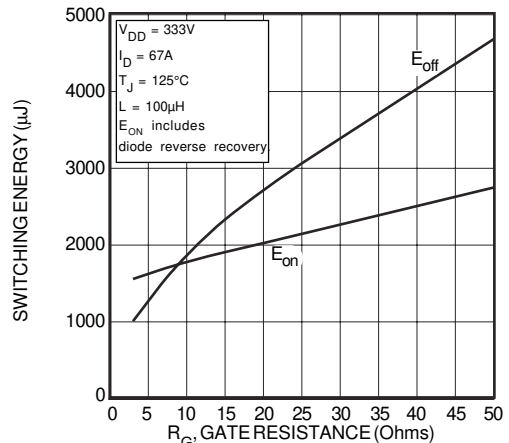


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

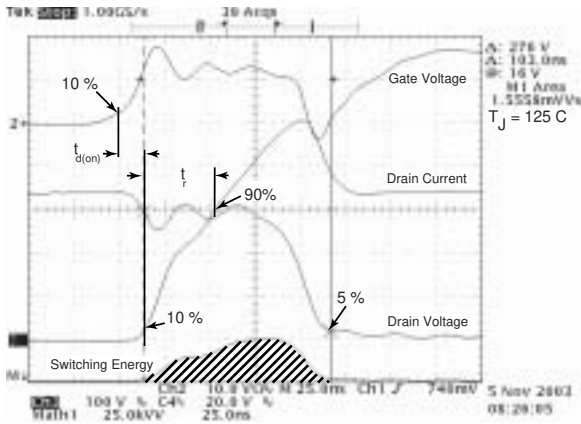


Figure 18, Turn-on Switching Waveforms and Definitions

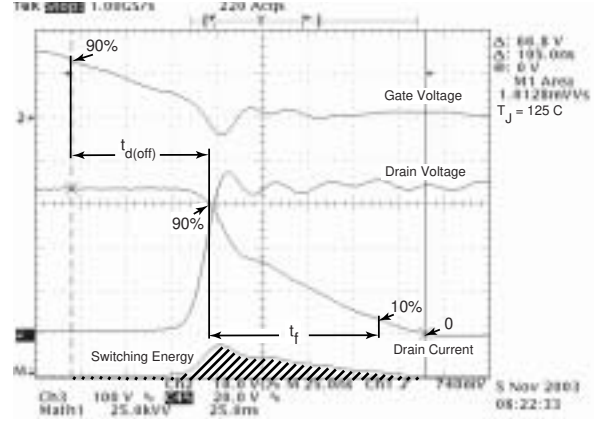


Figure 19, Turn-off Switching Waveforms and Definitions

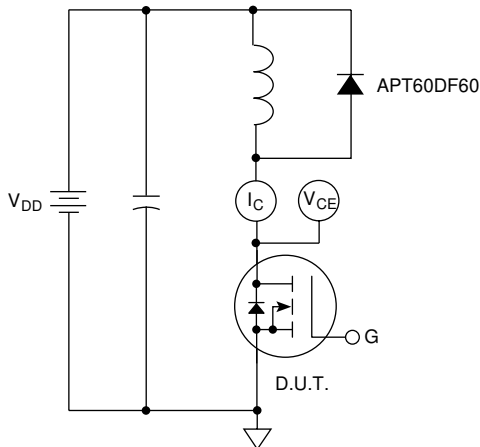
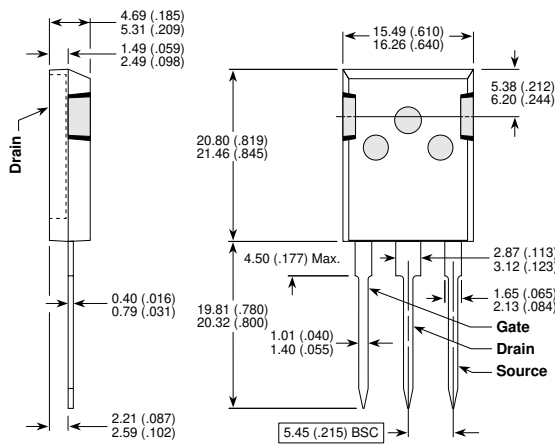


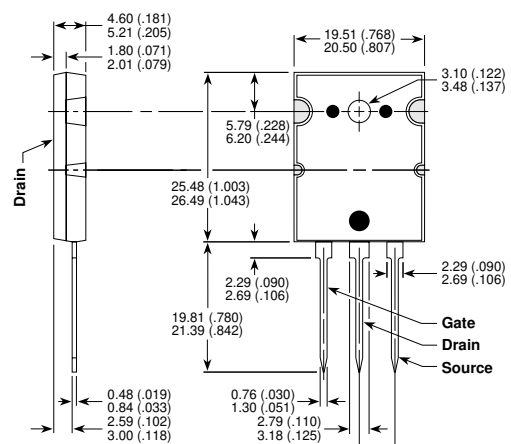
Figure 20, Inductive Switching Test Circuit

T-MAX® (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.
Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)